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Contents

xi *Conference Committee*

Part One

KEYNOTE SESSION

12496 03 **Overlay challenges in the era of high-NA (Keynote Paper)** [12496-1]

STOCHASTICS

12496 05 **Photoresist shrinkage observation by a metrological tilting-AFM** [12496-3]

12496 07 **Unbiased roughness measurements for 0.55NA EUV material setup** [12496-5]

12496 08 **SEMI-PointRend: improved semiconductor wafer defect classification and segmentation as rendering** [12496-6]

12496 09 **Overlay and edge placement error metrology in the era of stochastics** [12496-7]

OPTICAL METROLOGY

12496 0B **Full wafer OCD metrology: increasing sampling rate without the cost of ownership penalty** [12496-9]

12496 0C **Sensitivity analysis of optical scatterometry technique for high aspect ratio trench measurement** [12496-10]

12496 0D **TSV stress evolution mapping using in-line Raman spectroscopy** [12496-11]

12496 0E **Artificial-neural-network-assisted DUV scatterometry for OCD on HAR sub-micron structures** [12496-12]

12496 0F **Characterization of asymmetries in 3D NAND memory devices** [12496-13]

12496 0G **Curved-edge diffractive fringe pattern analysis for wafer edge metrology and inspection** [12496-182]

12496 0H **Using active asymmetry control and blind source separation to improve the accuracy of after develop overlay measurements** [12496-120]

OVERLAY

12496 0I **Alignment and overlay through opaque metal layers** [12496-15]

12496 0J **High spatial frequency on-device overlay characterization using CD-SEM contours** [12496-16]

12496 0K **SEM ADI on device overlay: the advantages and outcome** [12496-17]

12496 0L **Massive overlay metrology solution by realizing imaging Mueller matrix spectroscopic ellipsometry** [12496-18]

12496 0M **Machine learning robustness in overlay metrology** [12496-19]

EPE

12496 0N **EPE-aware process optimization for scanner dose and overlay in DRAM use case** [12496-20]

12496 0P **Multi-metrology: towards parametric yield predictions beyond EPE** [12496-22]

12496 0Q **Direct yield prediction from SEM images** [12496-114]

12496 0R **OPO improvements by Moiré effect-based imaging** [12496-24]

ELECTRON BEAM METROLOGY I

12496 0S **The rise of contour metrology from niche solution to versatile enabler (Invited Paper)** [12496-25]

12496 0T **Model validation for scanning electron microscopy** [12496-26]

12496 0U **Can remote SEM contours be used to match various SEM tools in fabs?** [12496-27]

12496 0W **Simulating HV-SEM imaging of HAR and buried features** [12496-29]

NEW METHODS

12496 0Y **A study on defect signal improvement using multi-scan optic patch images and new detection algorithm** [12496-31]

12496 0Z **EUV grazing-incidence lensless imaging wafer metrology** [12496-32]

12496 10 **Mueller matrix metrology with multi-angle information using multiple self-interference** [12496-33]

12496 11 **High-density CD measurement technology with high throughput and high precision on the entire surface of a process wafer, capable of capturing randomly occurring CD defects** [12496-34]

METROLOGY FOR THE EUV ERA

12496 12 **Dry resist metrology readiness for high-NA EUVL** [12496-35]

12496 13 **OPO robustness and measurability improvement via extended wavelengths** [12496-68]

12496 14 **Multi-modal tabletop EUV reflectometry for characterization of nanostructures (Karel Urbánek Best Student Paper Award)** [12496-37]

12496 15 **High repeatability and low shrinkage solution using CD-SEM for EUV resist** [12496-38]

3D AND HETEROGENEOUS INTEGRATION

12496 18 **Overlay performance in permanent bonded wafer integration schemes** [12496-40]

12496 19 **Characteristic Mueller matrix responses and correlation analysis for vertical GAA nanowire structure manufacturing using RCWA simulated spectra** [12496-84]

12496 1A **AI-guided OCD metrology for single HAR sub-micron via measurement** [12496-42]

12496 1B **Detection of bonding voids for 3D integration** [12496-43]

MACHINE LEARNING

12496 1C **Addressing misclassification costs in machine learning through asymmetric loss functions** [12496-44]

12496 1D **Self-supervised deep learning neural network for CD-SEM image denoising using reduced dataset** [12496-45]

12496 1E **Depth estimation from SEM images using deep learning and angular data diversity** [12496-103]

12496 1F **Semiconductor device metrology for detecting defective chip due to high aspect ratio-based structures using hyperspectral imaging and deep learning** [12496-47]

12496 1G **AI-guided optical-model-based superresolution for semiconductor CD metrology** [12496-48]

12496 1H **Deep learning-based automatic defect classification for semiconductor manufacturing** [12496-49]

EUV AND X-RAY METROLOGY

12496 1I **Soft x-ray: novel metrology for 3D profilometry and device pitch overlay (Invited Paper)** [12496-50]

12496 1J **Small target compatible dimensional and analytical metrology for semiconductor nanostructures using x-ray fluorescence techniques** [12496-51]

12496 1K **Critical dimension measurement: from synchrotron small angle x-ray scattering to industrial optical scatterometry techniques** [12496-52]

12496 1L **Reconstruction of the in-depth profile of line gratings with critical dimension grazing incidence small angle x-ray scattering on a laboratory equipment** [12496-53]

12496 1M **Pushing the boundaries of EUV scatterometry: reconstruction of complex nanostructures for next-generation transistor technology** [12496-54]

INSPECTION AND KAREL URBÁNEK BEST STUDENT PAPER AWARD PRESENTATION

12496 1N **A novel method for improving yield prediction by matching layout pattern and defect inspection** [12496-55]

12496 1O **In-situ electrical property quantification of memory devices by modulated electron microscopy** [12496-56]

12496 1P **Quantifying CD-SEM contact hole roughness and shape combined with machine learning-based pattern fidelity scores for process optimization and monitoring** [12496-57]

12496 1R **Novel depth quantification technique of buried defect for development of non-destructive optical inspection** [12496-59]

Part Two

ELECTRON BEAM METROLOGY II

12496 1T **Laser-assisted SEM for high-spatial resolution material metrology and inspection** [12496-61]

12496 1V **In-line metrology for vertical edge placement control of monolithic CFET using CD-SEM** [12496-63]

12496 1W **Advanced high-voltage e-beam system combined with an enhanced D2DB for on-device overlay measurement** [12496-166]

LATE BREAKING NEWS

12496 1X **300mm in-line metrologies for the characterization of ultra-thin layer of 2D materials** [12496-65]

12496 1Y **Detection of defective areas and hidden weak patterns in the wafer using massive measurement data** [12496-66]

12496 1Z **Measurement of W-recess profile in advanced node 3D NAND device with IRCD technology utilizing a specialized design-rule compliant target** [12496-85]

12496 20 **Enhancement of overlay metrology accuracy by multi-wavelength scatterometry with rotated quadrupole illumination** [12496-83]

POSTER SESSION

12496 22 **Tracing optimized condition for electron beam metrology of EUV photoresist pattern using low landing energy** [12496-136]

12496 24 **Scatterometry overlay (SCOL) measurement of small cell target using pupil optimization** [12496-67]

12496 25 **Machine-learning-based error detection modeling and feature scoring for error cause analysis of CD-SEMs** [12496-69]

12496 26 **Residuals reduction in imaging-based overlay using color per layer** [12496-70]

12496 27 **Optimizations of APC multivariate algorithm for linear mix and match overlay control** [12496-71]

12496 28 **Investigation of device overlay variation and control metrology in 3D-NAND process** [12496-72]

12496 29 **Novel electron beam technology using InGaN photocathode for high-throughput scanning electron microscope imaging** [12496-73]

12496 2A **Precise 3D profile measurement of high aspect ratio device patterns by small-angle x-ray scattering** [12496-74]

12496 2B **A study of high-accuracy stand-alone wafer metrology tool for high-productivity of exposure apparatus** [12496-75]

12496 2C **Enabling layer transfer and back-side power delivery network applications by wafer bonding and scanner correction optimizations** [12496-76]

12496 2D **Optimizing YOLOv7 for semiconductor defect detection** [12496-77]

12496 2E **ADI to in-cell overlay stability improvement for DRAM using novel scatterometry and comprehensive process control** [12496-78]

12496 2F **Absolute alignment measurement of underlayer and overlayer of diffraction-based overlay mark by image-based alignment metrology system** [12496-81]

12496 2I **Fourier analysis of spectrum for precision improvement in thickness determined by machine learning** [12496-88]

12496 2J **Numerical study of electromagnetic properties of the 3D through silicon via with high aspect ratio** [12496-90]

12496 2K **Frame generation methodology in mask tape-out flow and automation application** [12496-91]

12496 2L **Local depth monitoring using scanning electron microscopy and its verification using atomic force microscopy** [12496-92]

12496 2M **Small imaging overlay metrology targets for advance nodes** [12496-93]

12496 2N **Photoelectron beam technology for SEM imaging with pixel-specific control of irradiation beam current** [12496-94]

12496 2P **Edge detection using deep learning pipelines for TEM and SEM metrology by proposing generic and specific approaches** [12496-96]

12496 2Q **An optical critical dimension (OCD) model analysis on 3nm complementary FET (CFET) gate stacks** [12496-97]

12496 2R **Scatterometry and machine learning for in-die overlay solution** [12496-98]

12496 2S **On-line real-time detection system for wafer surface defects based on deep learning and generative adversarial network** [12496-99]

12496 2T **A generic deep-learning-based defect segmentation model for electron micrographs for automatic defect inspection** [12496-100]

12496 2U **The development of a machine learning-based excimer laser performance simulator for engineering maintenance decisions** [12496-101]

12496 2V **Mueller matrix spectroscopy and physics-based machine learning for gate-all-around sheet-specific metrology** [12496-102]

12496 2W **Determination of deep hole structure for advanced semiconductor devices analyzed by transmission x-ray scattering** [12496-104]

12496 2X **Wide-field massive CD metrology based on the imaging Mueller-matrix ellipsometry for semiconductor devices** [12496-105]

12496 2Y **A study of diffraction-based overlay (DBO) on a 3nm CFET metal layer** [12496-106]

12496 2Z **A study of 3nm CFET middle-of-the-line contact layer OCD measurement sensitivity** [12496-108]

12496 30 **Laser assisted SEM for visualizing electrical property using voltage contrast dynamics** [12496-109]

12496 31 **The role of neutral drag force in pulsed plasma enabled particle contamination control** [12496-112]

12496 32 **Wafer in process impact simulation caused by lens calibration** [12496-113]

12496 33 **Die-level nano-topography metrology to characterize the stress-induced in-plane distortion contribution to overlay** [12496-115]

12496 34 **Ultra-thin uncooled integrable-on-chip detector to measure wide infrared radiation residue in lithography exposure and metrology inspection tools** [12496-116]

12496 35 **Automatic defect classification (ADC) solution using data-centric artificial intelligence (AI) for outgoing quality inspections in the semiconductor industry** [12496-121]

12496 37 **Deep learning for the analysis of x-ray scattering data from high aspect ratio structures** [12496-123]

12496 38 **Parallel MEMS AFM for high-throughput semiconductor metrology and inspection** [12496-124]

12496 39 **Automated (S)TEM metrology characterization of gate-all-around and 3D NAND devices** [12496-128]

12496 3A **Parallax method for diffraction-based single-cell overlay and film thickness measurement** [12496-131]

12496 3B **Precise optical constant determination in the soft x-ray, EUV, and VUV spectral range** [12496-132]

12496 3C **Large field of view metrology: detecting critical edge placement error signatures not seen with small field of view in an HVM environment** [12496-133]

12496 3D **Advanced overlay metrology for 3D NAND bonding applications** [12496-134]

12496 3E **Tracing optimized condition for electron beam metrology of EUV photoresist pattern using low-landing energy** [12496-135]

12496 3F **Comparison between supervised and self-supervised deep learning for SEM image denoising** [12496-137]

12496 3G **New metrology technique for measuring the free shape of a patterned 300mm wafer held vertically** [12496-138]

12496 3J **AI-guided reliability diagnosis for 5,7nm automotive process** [12496-142]

12496 3K **Wafer yield prediction using AI: potentials and pitfalls** [12496-144]

12496 3M **3D measurement using SEM technology** [12496-60]

12496 3N **Exploiting spatial characteristic of wafer for effective OCW: area partitioning OCW** [12496-192]

12496 3O **Effective tool induced shift (eTIS) for determining the total measurement uncertainty (TMU) in overlay metrology** [12496-195]

12496 3P **General effective medium model for phonon heat flow in highly confined semiconductor nanosystems** [12496-196]

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